

Integrated Device Technology, Inc. 6024 Silver Creek Valley Road, San Jose, CA 95138

	024 Silver Creek Valley Ro C T/PROCESS C	PANGE NOTICE (PCN)
PCN #: N1508-01 Product Affected: 8T73S208-01NI 8T74S208-01NI (Refer to Table 2)	Date: September 21, 2015 LGI (8)	MEANS OF DISTINGUISHING CHANGED DEVICES: ■ Product Mark Change in ordering part# □ Back Mark □ Date Code □ Other
Date Effective: December 21, 2015 Contact: TSD Clock Team E-mail: clocks@idt.com		Attachment: Yes No Samples: Samples are available now.
DESCRIPTION AND PURPOSE OF ☐ Die Technology ☐ Wafer Fabrication Process ☐ Assembly Process ☐ Equipment ☐ Material ☐ Testing ☐ Manufacturing Site ■ Data Sheet ■ Other - Die Revision Change	This notice is to advise our 8T74S208A-01NLGI (8) i 01NLGI (8) to improve the operations. There is a minor change to manufacturing. The change	r customers that the IDT Part 8T73S208A-01NLGI (8) / is an updated version of the 8T73S208-01NLGI (8) / 8T74S208-e noise immunity for an overall better performance in I2C of the top metal. The is no change to the die/package technology or in datasheet parameters is shown in page 3 and page 4. The previous version by December 21, 2015.
RELIABILITY/QUALIFICATION There is no change in die technology/p		
to grant approval or request additiona it will be assumed that this change is a	written notification of this of a linformation. If IDT does nacceptable. ersion manufactured after the	change. Please use the acknowledgement below or E-Mail not receive acknowledgement within 30 days of this notice the process change effective date until the inventory
Customer:		Approval for shipments prior to effective date.
Name/Date:	E-	Mail Address:
Title:	Ph	none # /Fax #:
CUSTOMER COMMENTS:		
IDT ACKNOWLEDGMENT OF RI	ECEIPT:	
RECD. BY:		DATE:

PRODUCT/PROCESS CHANGE NOTICE (PCN)

ATTACHMENT 1 - PCN #: N1508-01

PCN Type: Die Revision Change / Datasheet

Data Sheet Change: Yes

Detail of Change: This notice is to advise our customers that the IDT Part 8T73S208A-01NLGI (8) / 8T74S208A-

01NLGI (8) is an updated version of the 8T73S208-01NLGI (8) / 8T74S208-01NLGI (8) to improve the

noise immunity for an overall better performance in I2C operations.

There is a minor change to the top metal. The is no change to the die/package technology or

manufacturing. The change in datasheet parameters is shown in page 3 and page 4.

We are requesting a last time buy of the previous version by December 21, 2015.

Table 1

Old Ordering Part Number	New Ordering Part Number
8T73S208-01NLGI	8T73S208A-01NLGI
8T73S208-01NLGI8	8T73S208A-01NLGI8
8T74S208-01NLGI	8T74S208A-01NLGI
8T74S208-01NLGI8	8T74S208A-01NLGI8

Qualification Test Plan and Result:

Qual Vehicle: 8T73S208A-01NLGI, 8T74S208A-01NLGI

Tost Description	Test Method (Latest	Test Results (SS / Rej)			
Test Description	specs in effect)	8T73S208A-01NLGI	8T74S208A-01NLGI		
ESD: Human Body Model @ 2000V	JS-001	3/0	3/0		
ESD: Charged Device Model @ 500V	JESD22-C101	3/0	3/0		
Latch-up	JESD78	6/0	6/0		

FROM

A)

8T73S208-01

 $\textbf{Table 4B. LVCMOS/LVTTL Input DC Characteristics, } V_{CC} = V_{CCO} = 2.5 \text{V} \pm 5\% \text{ or } 3.3 \text{V} \pm 5\%, V_{EE} = 0 \text{V}, T_{A} = -40 ^{\circ} \text{C to } 85 ^{\circ} \text{C}$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
VIH	Input High Voltage ¹		V _{CC} = 3.3V	2.2		V _{CC} + 0.3	V
VIH.			V _{CC} = 2.5V	1.7		V _{CC} + 0.3	V
VIL	Input Low Voltage ¹		V _{CC} = 3.3V	-0.3		0.8	V
VIL			V _{CC} = 2.5V	-0.3		0.7	V
I _{IH}	Input High Current	FSEL[1:0], ADR[1:0]	V _{CC} = V _{IN} = 2.625 or 3.465V			150	μА
		SCL, SDA	V _{CC} = V _{IN} = 2.625 or 3.465V			10	μΑ
I _{IL}	Input Low Current	FSEL[1:0], ADR[1:0]	V _{CC} = 2.625 or 3.465V, V _{IN} = 0V	-10			μА
	SCL, SDA		V _{CC} = 2.625 or 3.465V, V _{IN} = 0V	-150			μΑ

NOTE 1: V_{IL} should not be lower than -0.3V and V_{IH} should not be higher than V_{CC} + 0.3V.

TO 8T73S208A-01

Table 4B. LVCMOS/LVTTL Input DC Characteristics, $V_{CC} = V_{CCO} = 2.5V \pm 5\%$ or $3.3V \pm 5\%$, $V_{EE} = 0V$, $T_A = -40^{\circ}C$ to $85^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
	Input High Voltage ¹	FSEL[1:0], ADR[1:0]	$V_{CC} = 3.3V \pm 5\%$	2.2		V _{CC} + 0.3V	V
V _{IH}		SCL, SDA	$V_{CC} = 3.3V \pm 5\%$	2.4		V _{CC} + 0.3V	٧
		FSEL[1:0], ADR[1:0]	$V_{CC} = 2.5V \pm 5\%$	1.7		V _{CC} + 0.3V	V
		SCL, SDA	$V_{CC} = 2.5V \pm 5\%$	1.9		V _{CC} + 0.3V	V
	Input Low Voltage ¹	FSEL[1:0], ADR[1:0]	$V_{CC} = 3.3V \pm 5\%$	-0.3		0.8	V
V		SCL, SDA	$V_{CC} = 3.3V \pm 5\%$	-0.3		0.8	V
V _{IL}		FSEL[1:0], ADR[1:0]	$V_{CC} = 2.5V \pm 5\%$	-0.3		0.7	V
		SCL, SDA	$V_{CC} = 2.5V \pm 5\%$	-0.3		0.5	V
	Input High Current	FSEL[1:0], ADR[1:0]	V _{CC} = V _{IN} = 2.625 or 3.465V			150	μA
IH		SCL, SDA	V _{CC} = V _{IN} = 2.625 or 3.465V			10	μА
	Input Low Current	FSEL[1:0], ADR[1:0]	V _{CC} = 2.625 or 3.465V, V _{IN} = 0V	-10			μА
ılı		SCL, SDA	V _{CC} = 2.625 or 3.465V, V _{IN} = 0V	-150			μА

NOTE 1: V_{IL} should not be lower than -0.3V and V_{IH} should not be higher than V_{CC} + 0.3V.

FROM

B) 8T74S208-01

Table 4B. LVCMOS/LVTTL Input DC Characteristics, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40$ °C to 85°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{IH}	Input High Volta	age ¹		1.7		V _{DD} + 0.3	V
V _{IL}	Input Low Voltage ¹			-0.3		0.7	V
I _{IH}	Input High Current	FSEL[1:0], ADR[1:0]	V _{DD} = V _{IN} = 2.625			150	μА
		SCL, SDA	$V_{DD} = V_{IN} = 2.625$			5	μA
I _{IL}	Input Low Current	FSEL[1:0], ADR[1:0]	V _{DD} = 2.625, V _{IN} = 0V	-10			μА
		SCL, SDA	V _{DD} = 2.625, V _{IN} = 0V	-150			μA

NOTE: 1. V_{IL} should not be lower than -0.3V and V_{IH} should not be higher than V_{DD} + 0.3V.

TO 8T74S208A-01

Table 4B. LVCMOS/LVTTL Input DC Characteristics, $V_{DD} = V_{DDO} = 2.5V \pm 5\%$, $T_A = -40 ^{\circ} C$ to $85 ^{\circ} C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{IH}	Input High Voltage ¹	FSEL[1:0], ADR[1:0]	$V_{DD} = 2.5V \pm 5\%$	1.7		V _{CC} + 0.3V	V
	High voltage	SCL, SDA	$V_{DD} = 2.5V \pm 5\%$	1.9		V _{CC} + 0.3V	V
V _{IL}	Input Low Voltage ¹	FSEL[1:0], ADR[1:0]	$V_{DD} = 2.5V \pm 5\%$	-0.3		0.7	V
	Low voltage	SCL, SDA	$V_{DD} = 2.5V \pm 5\%$	-0.3		0.5	V
I _{IH}	Input High Current	FSEL[1:0], ADR[1:0]	$V_{DD} = V_{IN} = 2.625$			150	μА
		SCL, SDA	$V_{DD} = V_{IN} = 2.625$			5	μA
I _{IL}	Input Low Current	FSEL[1:0], ADR[1:0]	$V_{DD} = 2.625, V_{IN} = 0V$	-10			μА
		SCL, SDA	$V_{DD} = 2.625, V_{IN} = 0V$	-150			μA

NOTE 1: V_{IL} should not be lower than -0.3V and V_{IH} should not be higher than V_{DD} + 0.3V.